/ Descriptions

SOT-23 PNP Silicon PNP transistor in a SOT-23 Plastic Package.

/ Features

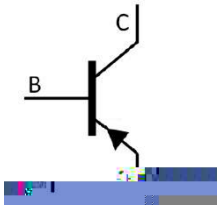
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Low saturation voltage, large collector current.

/ Applications

General purpose amplifier and muting switch application.

/ Equivalent Circuit



/ Pinning



PIN1 Base PIN 2 Emitter PIN 3 Collector

/ h_{FE} Classifications & Marking

h_{FE} Classifications
Symbol

/ Absolute Maximum Ratings(Ta=25)

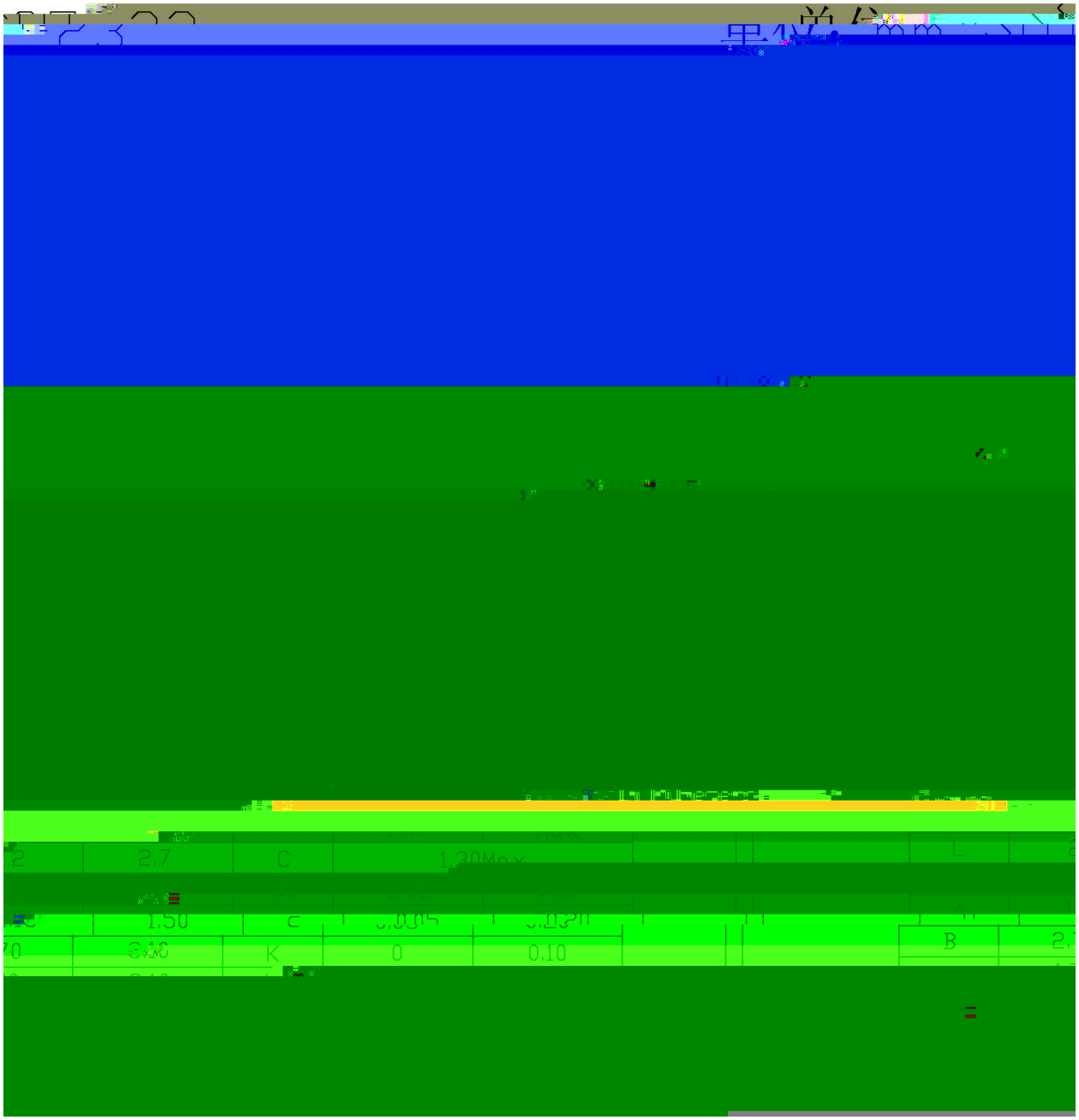
Parameter	Symbol	Rating	Unit
Collector to Base Voltage	V_{CBO}	-15	V
Collector to Emitter Voltage	V_{CEO}	-12	V
Emitter to Base Voltage	V_{EBO}	-5.0	V
Collector Current	I_C	-400	mA
Base Current	I_B	-50	mA
Collector Power Dissipation	P_C	100	mW
Junction Temperature	T_j	150	
Storage Temperature Range	T_{stg}	-55 150	

/ Electrical Characteristics(Ta=25)

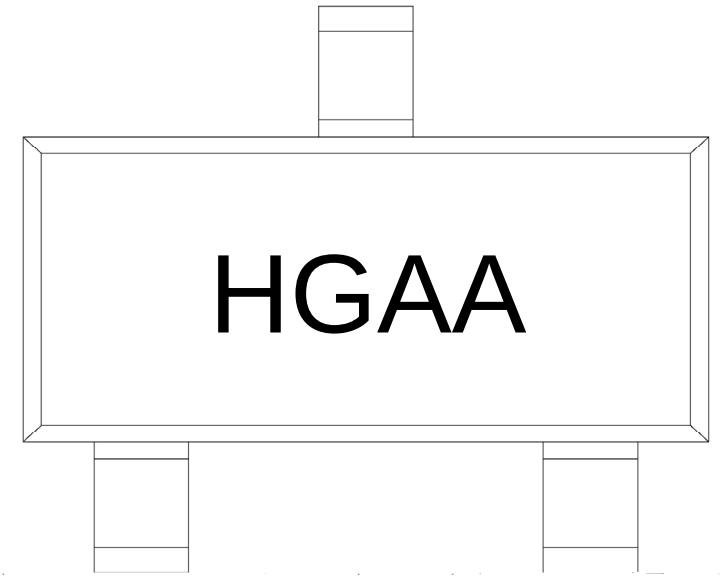
Parameter		Symbol	Test Conditions	Min	Typ	Max	Unit
Collector Cut-Off Current		I_{CBO}	V_{CB}=-15V I_E=0			-0.1	A
Emitter Base Cut-Off Current		I_{EBO}	V_{EB}=-5.0V I_c=0			-0.1	A
DC Current Gain		h_{FE}	V_{CE}=-2.0V I_C=-10mA	300		1000	
Collector to Emitter Saturation Voltage		$V_{CE(sat)(1)}$	I_C=-10mA I_B=-0.5mA		-0.015	-0.03	V
		$V_{CE(sat)(2)}$	I_C=-200mA I_B=-10mA		-0.11	-0.25	V
Base to Emitter Saturation Voltage		$V_{BE(sat)}$	I_C=-200mA I_B=-10mA		-0.87	-1.2	V
Transition Frequency		f_T	V_{CE}=-2.0V I_E=-10mA	80	130		MHz
Collector Output Capacitance		C_{ob}	V_{CB}=-10V I_E=0 f=1.0MHz		4.2		pF
Collector-Emitter On Resistance		R_{on}	I_B=-1.0mA V_{in}=-1.0V V_{rms}f=1KHz		0.9		
Switching time	Turn-On Time	t_{on}	I_{B1}=-I_{B2}=5.0mA		40		ns
	Storage Time	T_{stg}			280		
	Fall Time	t_f			45		

/ Electrical Characteristic Curve

/ Package Dimensions



/ Marking Instructions



H

GA

A: h_{FE}

Note:

H: Company Code.

GA: Product Type Code

A: h_{FE} Classifications Symbol Code

( ) / Temperature Profile for IR Reflow Soldering(Pb Z